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Symbol	Parameter	Max.	Units	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	150		
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	95	А	
I _{DM}	Pulsed Drain Current	600		
P _D @T _C = 25°C	Power Dissipation	125	W	
V _{DS} Drain-Source Voltage		30	V	
V _{GS}	Gate-to-Source Voltage	± 20	V	
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C	



Symbol	Characterizes	Тур.	Max.	Units
	Junction-to-case			

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	30			V	$V_{GS} = 0V, I_D$

 $R_{DS(on)} \qquad \text{Static Drain-to-Source on-}$







Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.







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